

Growth mode and strain effect on relaxor ferroelectric domains in epitaxial 0.67Pb(Mg_{1/3}Nb_{2/3})O₃-0.33PbTiO₃/SrRuO₃ heterostructures

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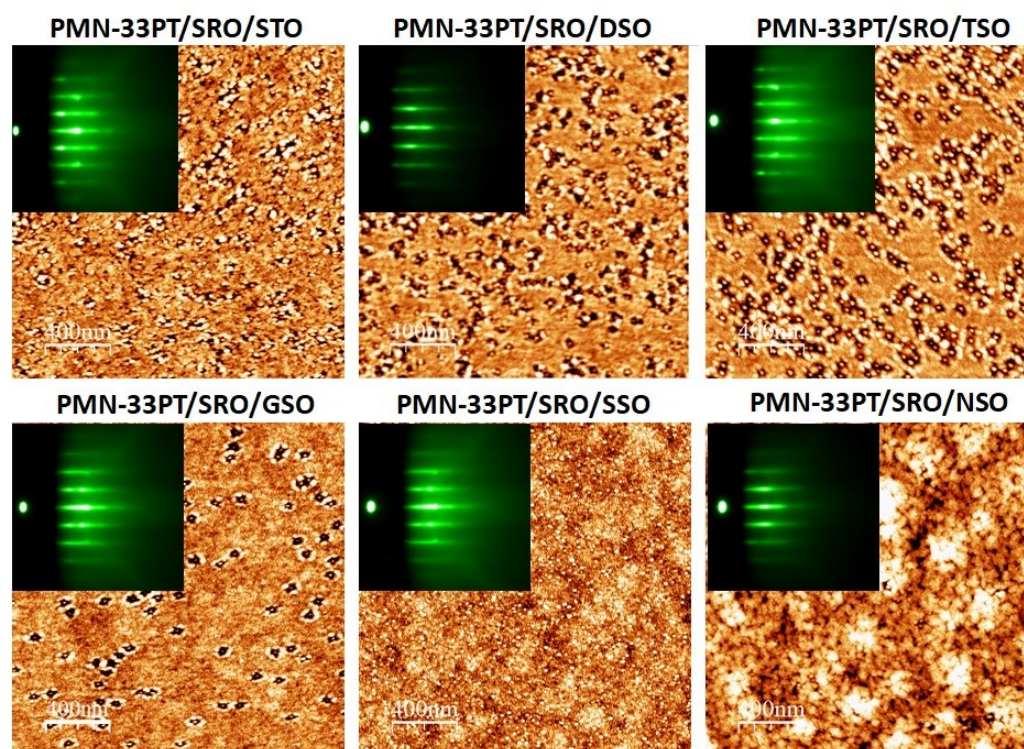


FIG. S1. AFM topography at room temperature of the surface of the as-grown PMN-33PT/SRO/STO and PMN-33PT/SRO/ReScO₃ (Re=DSO, TSO, GSO, SSO, and NSO) heterostructures. The insets show the corresponding RHEED pattern of the PMN-33PT layers.

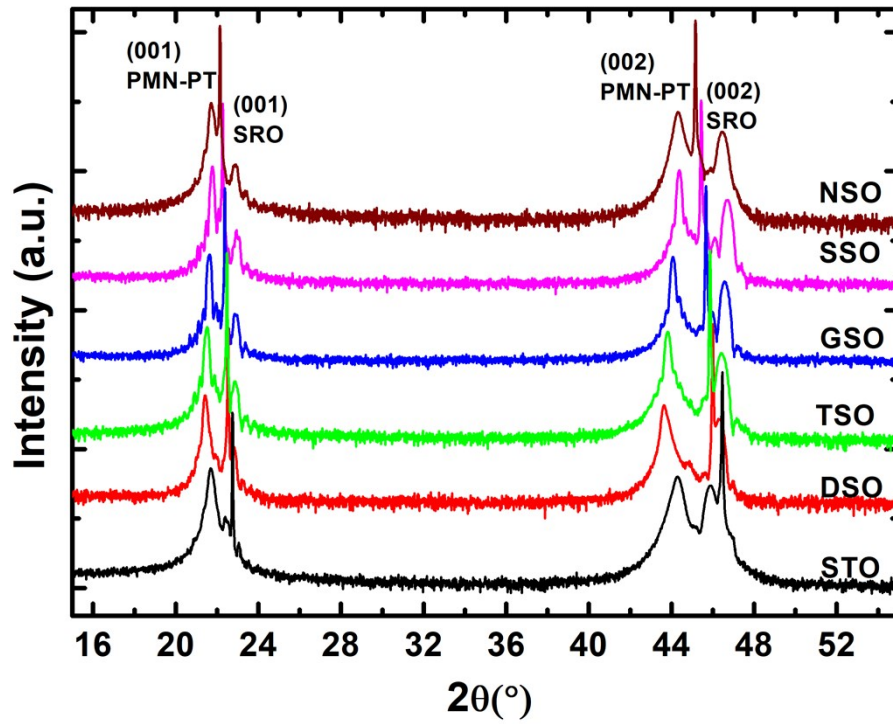


FIG. S2. θ - 2θ XRD patterns in the range 15 - 55° of PMN-33PT/SRO/(STO and ReScO_3) heterostructures showing single-phase and pyrochlore-free samples.

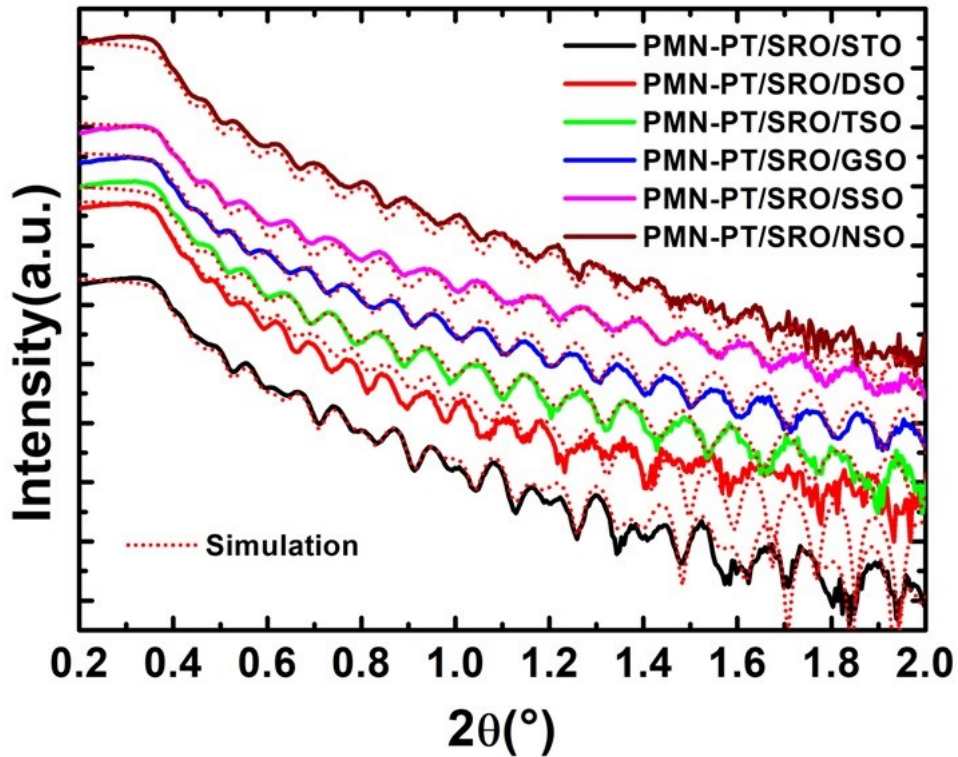


FIG. S3. X-ray reflectivity diagrams of PMN-33PT/SRO/(STO and ReScO_3) heterostructures.

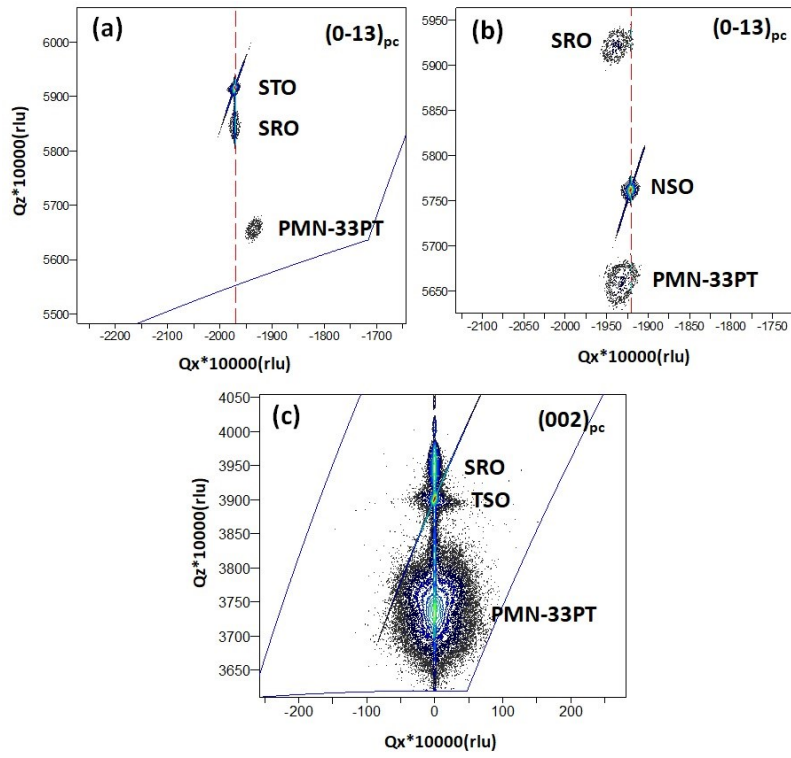


FIG. S4. RSMs of PMN-33PT/SRO/STO (a) and PMN-33PT/SRO/NSO (b) around $(0-13)_{pc}$ and of PMN-33PT/SRO/TSO (c) around $(002)_{pc}$.